



Title of Change:	Hydrazine elimination in ON Semiconductor Niigata Co., Ltd., Japan (OSNC).													
Proposed first ship date:	19 March 2019													
Contact information:	Contact your local ON Semiconductor Sales Office or <Yukio.Kudo@onsemi.com>													
Samples:	Contact your local ON Semiconductor Sales Office or <PCN.samples@onsemi.com> Sample requests are to be submitted no later than 30 days from the date of first notification, Initial PCN or Final PCN, for this change.													
Additional Reliability Data:	Contact your local ON Semiconductor Sales Office or <Satoru.Fujinuma@onsemi.com>													
Type of notification:	This is a Final Product/Process Change Notification (FPCN) sent to customers. FPCNs are issued 90 days prior to implementation of the change. ON Semiconductor will consider this change accepted, unless an inquiry is made in writing within 30 days of delivery of this notice. To do so, contact <PCN.Support@onsemi.com>													
Change Part Identification:	Date Code													
Change Category:	<input checked="" type="checkbox"/> Wafer Fab Change <input type="checkbox"/> Assembly Change <input type="checkbox"/> Test Change <input type="checkbox"/> Other _____													
Change Sub-Category(s):	<input type="checkbox"/> Manufacturing Site Addition <input type="checkbox"/> Material Change <input type="checkbox"/> Datasheet/Product Doc change <input type="checkbox"/> Manufacturing Site Transfer <input type="checkbox"/> Product specific change <input type="checkbox"/> Shipping/Packaging/Marking <input checked="" type="checkbox"/> Manufacturing Process Change <input type="checkbox"/> Other: _____													
Sites Affected:	ON Semiconductor Sites: ON Niigata, Japan	External Foundry/Subcon Sites: None												
Description and Purpose:														
<p>This final notification announces the elimination of Hydrazine in ON Semiconductor Niigata Co., Ltd. Japan for parts listed in this PCN.</p> <p>Hydrazine was identified as a prohibited chemical in ON Semiconductor as it is considered as a carcinogenic substance and has high risk of fire and explosion.</p> <p>The related products are transferred to a process that does not use Hydrazine on the same site ON Semiconductor Niigata, Japan (OSNC).</p>														
	<table border="1"> <thead> <tr> <th>Change Point</th> <th>Before Change Description</th> <th>After Change Description</th> </tr> </thead> <tbody> <tr> <td>Fab (OSNC)</td> <td>N1 Fab (Minimum rule=0.8um, Class=10)</td> <td>N1 Fab (Minimum rule=0.8um, Class=10) AND N2 Fab (Minimum rule=0.25um, Class=1)</td> </tr> <tr> <td>Wire material</td> <td>Aluminum (without Anti-reflected Layer)</td> <td>Aluminium (with Anti-reflected Layer)</td> </tr> <tr> <td>Interlayer material</td> <td>Silicon nitride and Polyimide or Polyimide</td> <td>Silicon nitride and Silicon oxide or Oxide</td> </tr> </tbody> </table>		Change Point	Before Change Description	After Change Description	Fab (OSNC)	N1 Fab (Minimum rule=0.8um, Class=10)	N1 Fab (Minimum rule=0.8um, Class=10) AND N2 Fab (Minimum rule=0.25um, Class=1)	Wire material	Aluminum (without Anti-reflected Layer)	Aluminium (with Anti-reflected Layer)	Interlayer material	Silicon nitride and Polyimide or Polyimide	Silicon nitride and Silicon oxide or Oxide
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Reliability Data Summary:

QV DEVICE NAME : LB11870-TRM-E

RMS :J43387

PACKAGE:HSSOP48(375mil)

Test	Specification	Condition	Interval	Results
HTOL	JESD22-A108	Tj=150°C, 100 % max rated Vcc	1008 hrs	0/77
HTSL	JESD22-A103	Ta= 150°C	1008 hrs	0/77
TC	JESD22-A104	Ta= -65°C to +150°C	500 cyc	0/77
THB	JESD22-A101	85°C, 85% RH, bias	1008 hrs	0/77
uHAST	JESD22-A118	130°C, 85% RH, 18.8psig,	96 hrs	0/77
PC	J-STD-020 JESD-A113	MSL 3 @ 260 °C	-	PASS
HBM	JS001	100pF,1.5kohm,+/-1kV	-	0/3
CDM	JS002	+/-500V	-	0/3

Electrical Characteristic Summary: There is no change in the electrical performance. Datasheet specifications remain unchanged.

List of Affected Parts:

Part Number	Qualification Vehicle
LA6584JA-AH	LB11870-TRM-E
LA6584M-TLM-H	
LB11964FA-BH	
LB11870-TRM-E	
LB11961V-TLM-H	
LB1862MC-AH	
LB1836M-TLM-E	
LB1838M-TRM-E	
LB1843V-TLM-E	
LB1935FA-BH	
LB1938FA-BH	
LA6588MC-AH	
LB1836ML-TLM-E	
LA6584M-TLM-E	
LB1838M-TLM-E	
LB11961V-TLM-E	

NOTE:

Please be informed that there are Customer Specific parts impacted by this notice, thus MPN & CPN info will not be reflected in the parts list of this Generic document. Instead please click the link to the addendum copy provided in the email notification to see full list of affected products specific to your company.

Japanese translation of the notification starts here.
通知の日本語訳はここから始まります。

Note: The Japanese version is for reference only. In case of any differences between the English and Japanese version, the English version shall control.

注：日本語版は参照用です。英語版と日本語版の違いがある場合は、英語版が優先されます。



信頼性データの要約:

QV 素子名: LB11870-TRM-E

RMS :J43387

パッケージ: HSSOP48(375mil)

テスト	仕様	条件	間隔	結果
HTOL	JESD22-A108	Tj=150°C, 100 % max rated Vcc	1008 hrs	0/77
HTSL	JESD22-A103	Ta= 150°C	1008 hrs	0/77
TC	JESD22-A104	Ta= -65°C to +150°C	500 cyc	0/77
THB	JESD22-A101	85°C, 85% RH, bias	1008 hrs	0/77
uHAST	JESD22-A118	130°C, 85% RH, 18.8psig,	96 hrs	0/77
PC	J-STD-020 JESD-A113	MSL 3 @ 260 °C	-	PASS
HBM	JS001	100pF,1.5kohm,+/-1kV	-	0/3
CDM	JS002	+/-500V	-	0/3

電気的特性の要約: 電気的性能に変更はありません。データシートの仕様に変更はありません。

影響を受ける部品の一覧:

部品番号	品質試験用ピークル
LA6584JA-AH	LB11870-TRM-E
LA6584M-TLM-H	
LB11964FA-BH	
LB11870-TRM-E	
LB11961V-TLM-H	
LB1862MC-AH	
LB1836M-TLM-E	
LB1838M-TRM-E	
LB1843V-TLM-E	
LB1935FA-BH	
LB1938FA-BH	
LA6588MC-AH	
LB1836ML-TLM-E	
LA6584M-TLM-E	
LB1838M-TLM-E	
LB11961V-TLM-E	

注: 本通知により影響を受ける顧客特定部品があり、よって MPN および CPN 情報は本一般文書の部品リストに反映していないことにご留意ください。代わりに、特に御社に影響する製品の全リストを見るためには電子メール通知で提供される補遺コピーへのリンクをクリックしてください。